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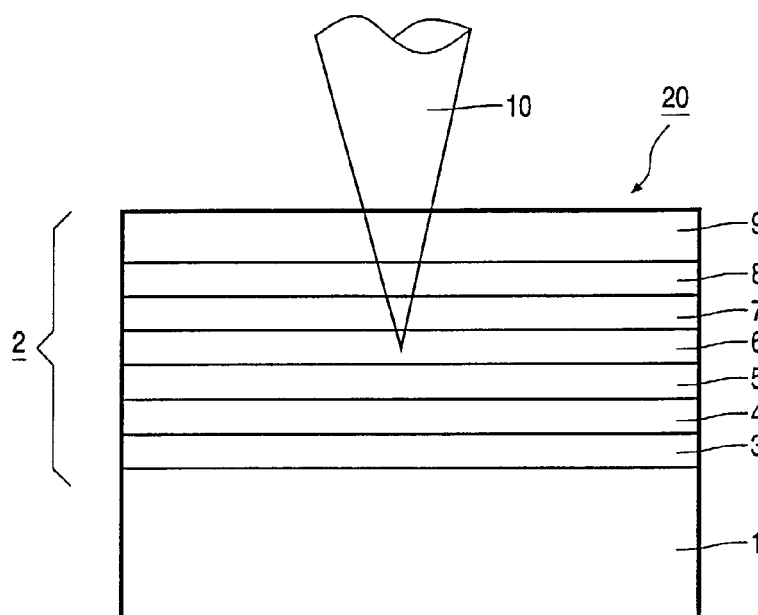
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(54) Title: OPTICAL INFORMATION MEDIUM AND ITS USE



(57) Abstract: An optical information medium (20) for high speed erasable recording by means of a laser-light beam (10) is provided. A substrate (1) has a stack (2) of layers with a first dielectric layer (5) and a second dielectric layer (7), a phase-change recording layer (6) between the first dielectric layer (5) and the second dielectric layer (7), and a reflective layer (3). The recording layer (6) has a compound of Ge and Te, and at least the first dielectric layer (5) consists of oxides of Ta and Si, nitrides of Si and Al, or carbides of Si, and is in contact with the recording layer (6). The recording layer (6) additionally may contain O or N in an amount up to 5 at. %. A broad usable composition range for low CET values is obtained. Thus high data rates are achieved.

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